

제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

F. Silicon and Group-IV Devices and Integration Technology 분과

Room C
함백 I (5층)

2016년 2월 23일(화) 08:30-10:30

[TC1-F] Novel Si Devices and Integrated Circuits (4)

좌장 : 남동욱(인하대학교), 신창환(서울시립대학교)

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| TC1-F-1 | 08:30-08:45 | Advanced Bulk CMOS Technology-based Standard Ternary Inverter for Compact Multi-valued Analog-to-Digital Converter Sunhae Shin and Kyung Rok Kim <i>School of Electrical and Computer Engineering, Ulsan National Institute of Science and Technology</i> |
| TC1-F-2 | 08:45-09:00 | Effects of Channel Hole Diameter and Blocking Layer Thickness on Electrical Characteristics in Word-Line Stacked NAND Flash Memory Sang-Ho Lee, Dae Woong Kwon, Seung-Hyun Kim, Myung Hyun Baek, and Byung-Gook Park <i>Department of Electrical and Computer Engineering, Seoul National University</i> |
| TC1-F-3 | 09:00-09:15 | 15mV/decade Steep Switching Device using Topological Insulator Hyunwoo Choi and Changhwan Shin <i>School of Electrical and Computer Engineering, University of Seoul</i> |
| TC1-F-4 | 09:15-09:30 | Novel Asymmetric Channel in a Self-Aligned 65-nm CMOS Technology for High-Performance of Plasmonic Terahertz Wave Detector Min Woo Ryu, Kwan Sung Kim, Jeong Seop Lee, Sang Hyo Ahn, Hyung Ju Jeon, and Kyung Rok Kim <i>School of Electrical and Computer Engineering, Ulsan National Institute of Science and Technology</i> |